

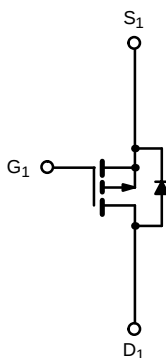
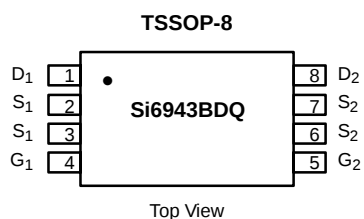


New Product

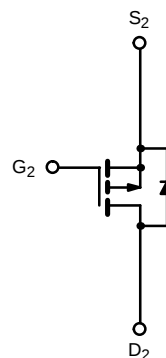
Si6943BDQ
 Vishay Siliconix

Dual P-Channel 2.5-V (G-S) MOSFET

PRODUCT SUMMARY		
V_{DS} (V)	$r_{DS(on)}$ (Ω)	I_D (A)
-12	0.08 @ $V_{GS} = -4.5$ V	-2.5
	0.105 @ $V_{GS} = -2.5$ V	-1.9

TrenchFET®
 Power MOSFETs


DataSheet4U.com P-Channel MOSFET



P-Channel MOSFET

ABSOLUTE MAXIMUM RATINGS (T _A = 25°C UNLESS OTHERWISE NOTED)					
Parameter		Symbol	10 secs	Steady State	Unit
Drain-Source Voltage		V _{DS}	-12		V
Gate-Source Voltage		V _{GS}	±8		
Continuous Drain Current (T _J = 150°C) ^a	T _A = 25°C	I _D	- 2.5	-2.3	A
	T _A = 70°C		-2.2	-1.8	
Pulsed Drain Current (10 μs Pulse Width)		I _{DM}	-20		
Continuous Source Current (Diode Conduction) ^a		I _S	-1.0	-0.7	
Maximum Power Dissipation ^a	T _A = 25°C	P _D	1.10	0.80	W
	T _A = 70°C		0.70	0.50	
Operating Junction and Storage Temperature Range		T _J , T _{stg}	-55 to 150		°C

THERMAL RESISTANCE RATINGS					
Parameter		Symbol	Typical	Maximum	Unit
Maximum Junction-to-Ambient ^a	$t \leq 10$ sec	R_{thJA}	89	110	$^\circ\text{C/W}$
	Steady State		120	150	
Maximum Junction-to-Foot (Drain)	Steady State	R_{thJF}	70	90	

Notes

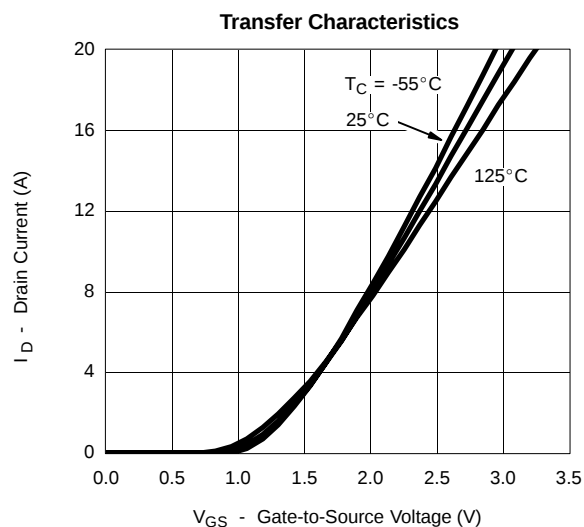
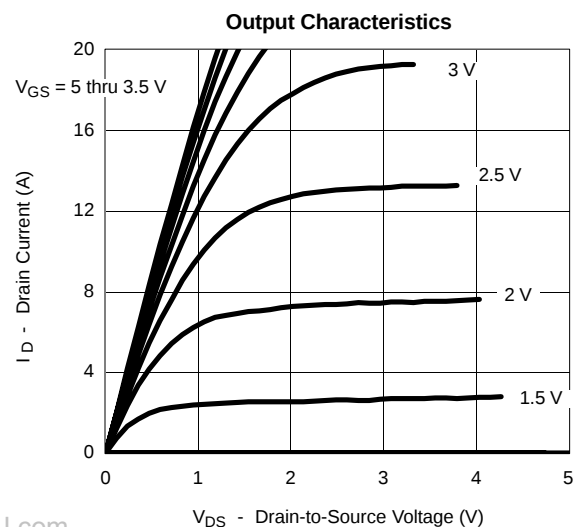
^a Surface Mounted on 1" x 1" FR4 Board.

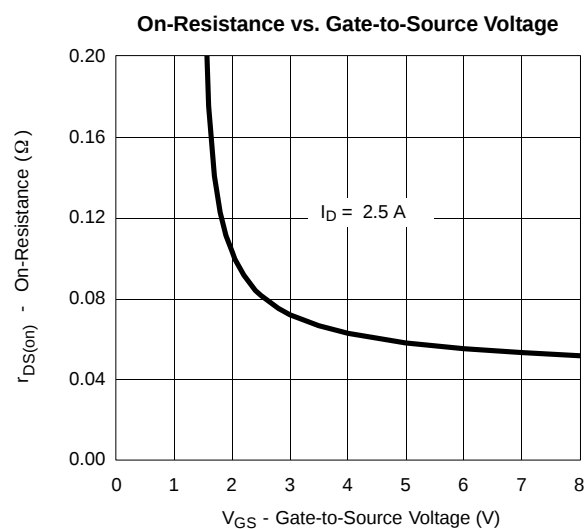
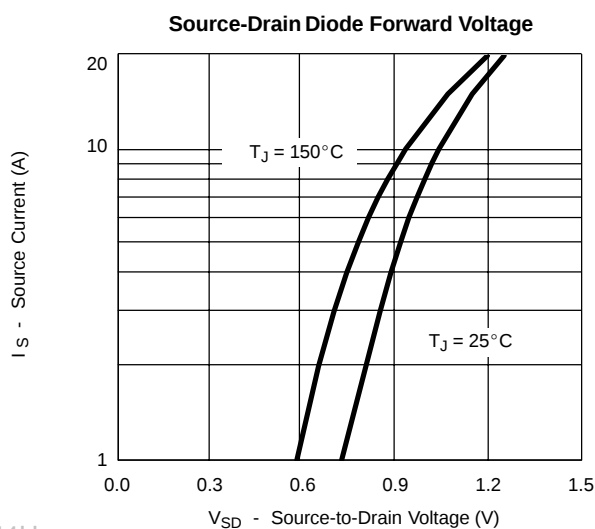
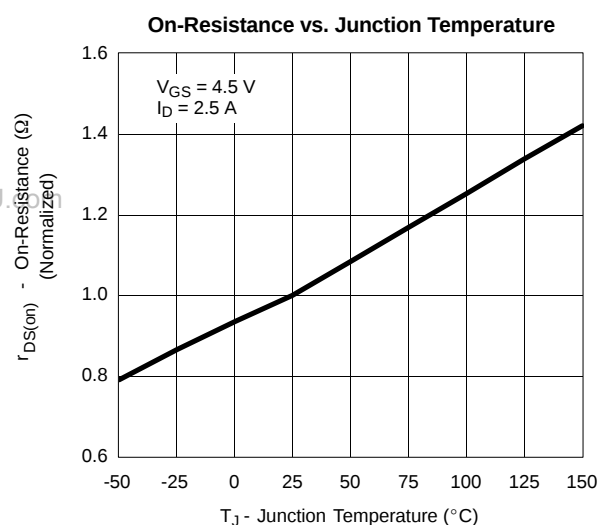
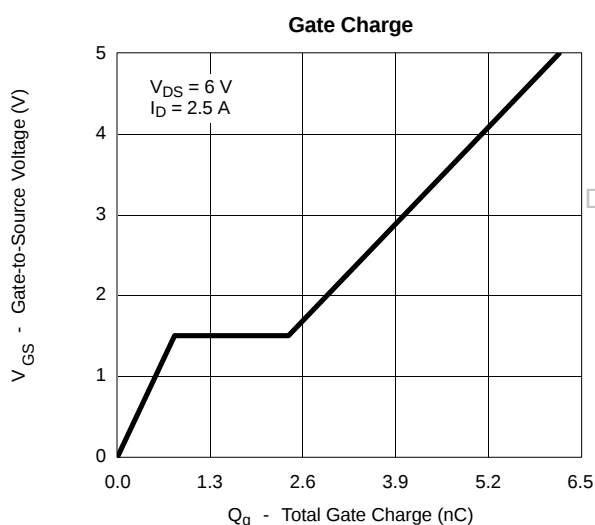
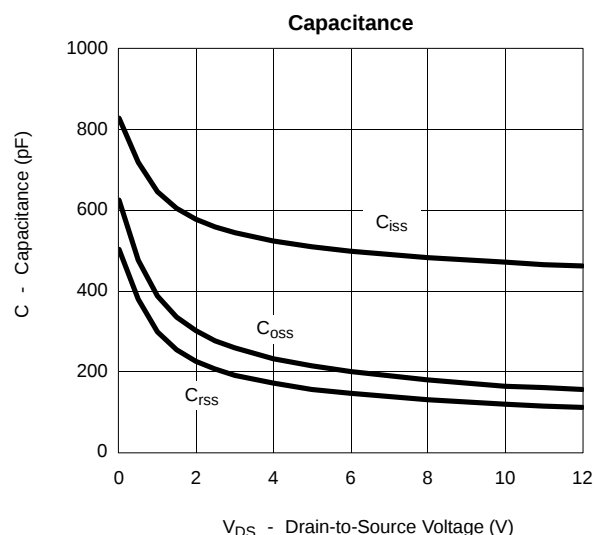
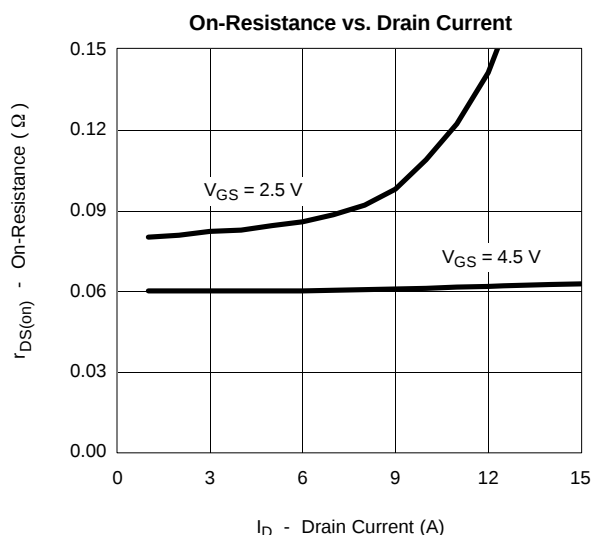
Si6943BDQ**Vishay Siliconix****New Product****SPECIFICATIONS ($T_J = 25^\circ\text{C}$ UNLESS OTHERWISE NOTED)**

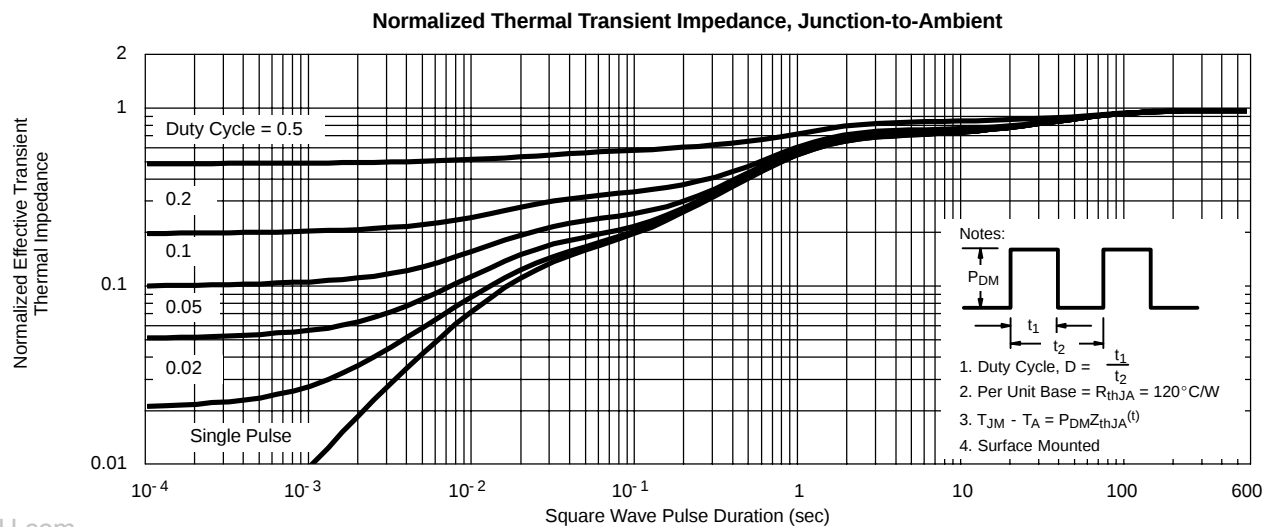
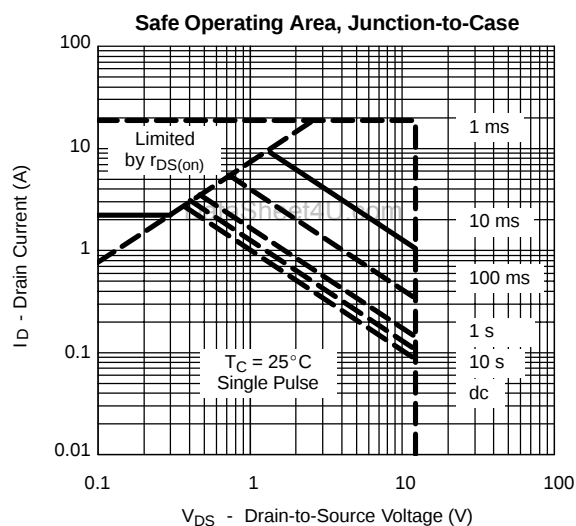
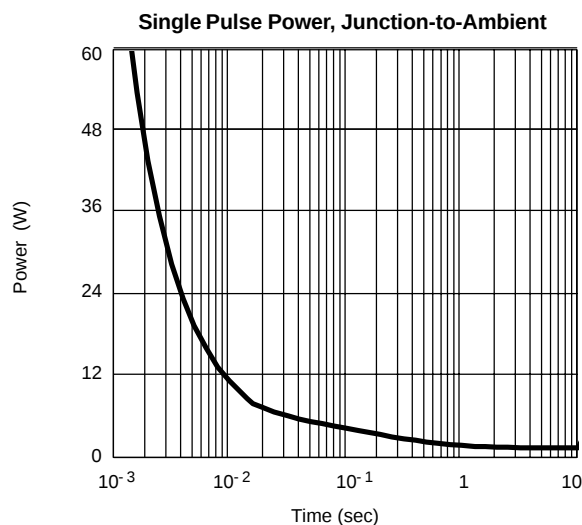
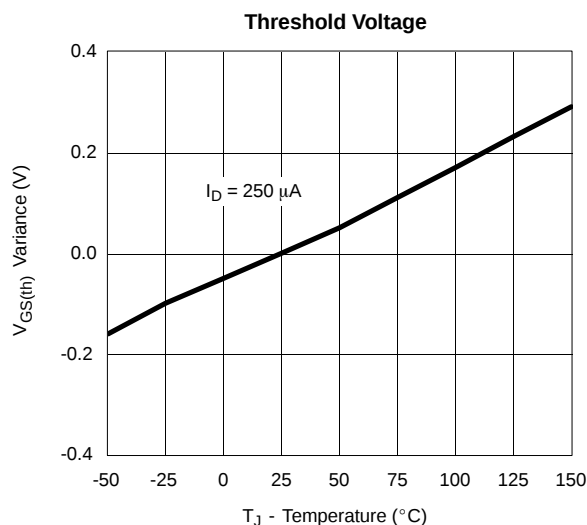
Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Static						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS} = V_{GS}$, $I_D = -250\ \mu\text{A}$	-0.45		-0.8	V
Gate-Body Leakage	I_{GSS}	$V_{DS} = 0\ \text{V}$, $V_{GS} = \pm 8\ \text{V}$			± 100	nA
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS} = -9.6\ \text{V}$, $V_{GS} = 0\ \text{V}$			-1	μA
		$V_{DS} = -9.6\ \text{V}$, $V_{GS} = 0\ \text{V}$, $T_J = 70^\circ\text{C}$			-5	
On-State Drain Current ^a	$I_{D(on)}$	$V_{DS} = -5\ \text{V}$, $V_{GS} = -4.5\ \text{V}$	-10			A
Drain-Source On-State Resistance ^a	$r_{DS(on)}$	$V_{GS} = -4.5\ \text{V}$, $I_D = -2.5\ \text{A}$		0.06	0.08	Ω
		$V_{GS} = -2.5\ \text{V}$, $I_D = -1.9\ \text{A}$		0.08	0.105	
Forward Transconductance ^a	g_{fs}	$V_{DS} = -15\ \text{V}$, $I_D = -2.5\ \text{A}$		8		S
Diode Forward Voltage ^a	V_{SD}	$I_S = -1.0\ \text{A}$, $V_{GS} = 0\ \text{V}$		-0.75	-1.2	V
Dynamic^b						
Total Gate Charge	Q_g	$V_{DS} = -6\ \text{V}$, $V_{GS} = -4.5\ \text{V}$, $I_D = -2.5\ \text{A}$		5.7	10	nC
Gate-Source Charge	Q_{gs}			0.8		
Gate-Drain Charge	Q_{gd}			1.6		
Turn-On Delay Time	$t_{d(on)}$	$V_{DD} = -6\ \text{V}$, $R_L = 6\ \Omega$ $I_D = 1.0\ \text{A}$, $V_{GEN} = -4.5\ \text{V}$, $R_G = 6\ \Omega$		15	25	ns
Rise Time	t_r			35	60	
Turn-Off Delay Time	$t_{d(off)}$			35	60	
Fall Time	t_f			30	50	
Source-Drain Reverse Recovery Time	t_{rr}	$I_F = -1.0\ \text{A}$, $di/dt = 100\ \text{A}/\mu\text{s}$		30	60	

Notes

- a. Pulse test; pulse width $\leq 300\ \mu\text{s}$, duty cycle $\leq 2\%$.
b. Guaranteed by design, not subject to production testing.

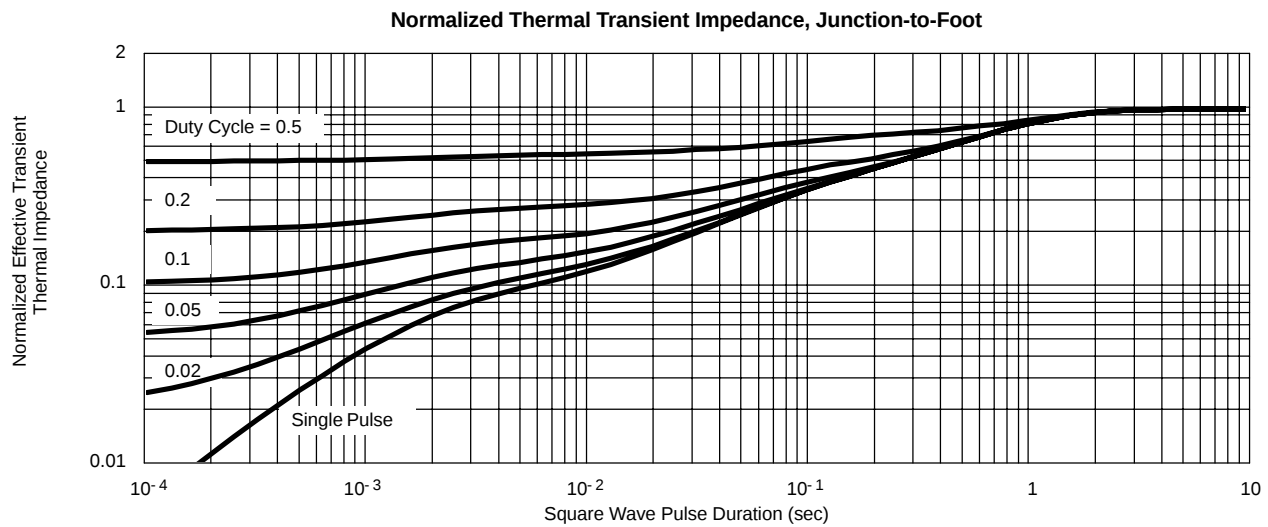
TYPICAL CHARACTERISTICS (25°C UNLESS NOTED)


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Si6943BDQ**Vishay Siliconix****New Product****TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)**



New Product

Si6943BDQ
Vishay Siliconix**TYPICAL CHARACTERISTICS (25 °C UNLESS NOTED)**

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